



# **Asymmetric Thyristor**

 $V_{DRM}$ 

I<sub>T(RMS)</sub>

I<sub>TSM</sub> dVdt

dl/dt

Replaces March 1998 version, DS4680-2.1

DS4680-3.0 January 2000

**KEY PARAMETERS** 

1400V

370A

2000A

1000V/μs

**1000A/μs 7.0**μs

## **APPLICATIONS**

- High Frequency Applications
- High Power Choppers And Inverters
- Welding
- Ultrasonic Generators
- Induction Heating
- 400Hz UPS
- PWM Inverters

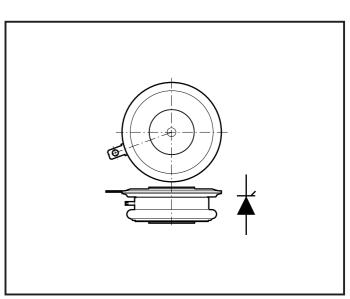
## **FEATURES**

- Low Loss Asymmetrical Diffusion Structure
- High Interdigitated Amplifying Gate
- Gate Assisted Turn-off With Exclusive Bypass Diode
- Fully Characterised For Operation up to 40kHz
- Directly Compatible With 220-480 A.c. Mains

#### **VOLTAGE RATINGS**

Type Number	Repetitive Peak Off-state Voltage V	Repetitive Peak Reverse Voltage V <sub>RRM</sub> V
TA329 14 Q	1400	10
TA329 12 Q	1200	10
TA329 10 Q	1000	10

Lower voltage grades available.



Outline type code: MU86. See Package Details for further information.

# **CURRENT AND SURGE RATINGS**

Symbol	Parameter	Parameter Conditions		Units
Double Sid	e Cooled			
I <sub>T(RMS)</sub>	RMS value	Half sine wave, duty cycle 50%, $T_{case} = 80^{\circ}C$ , $T_{j} = 125^{\circ}C$ .	370	Α
I <sub>TSM</sub>	Surge (non-repetitive) on-state current	$T_j = 125^{\circ}C, t_p = 1 \text{ms}, V_R = 0$	2000	А
l²t	I <sup>2</sup> t for fusing	t <sub>p</sub> ≥ 10ms	20 x 10 <sup>3</sup>	A²s

TA329..Q

# THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions		Min.	Max.	Units
		Double side cooled	dc	-	0.085	°C/W
R <sub>th(j-c)</sub>	Thermal resistance - junction to case	Single side cooled	Anode dc	-	0.153	°C/W
			Cathode dc	-	0.204	°C/W
ь	Thermal resistance - case to heatsink	Clamping force 4.0kN with mounting compound	Double side	-	0.02	°C/W
R <sub>th(c-h)</sub>			Single side	-	0.04	°C/W
_	On-state (conduc			-	135	°C
T <sub>vj</sub>	Virtual junction temperature	Reverse (blocking)		-	125	°C
T <sub>stg</sub>	Storage temperature range			-40	150	°C
-	Clamping force			3.6	4.4	kN

# **DYNAMIC CHARACTERISTICS**

Symbol	Parameter	Conditions		Min.	Max.	Units
V <sub>TM</sub>	Maximum on-state voltage	At 600A peak, T <sub>case</sub> = 125°C		-	2.5	V
I <sub>RRM</sub>	Peak reverse current	At V <sub>RRM</sub> , T <sub>case</sub> = 125°C	At V <sub>RRM</sub> , T <sub>case</sub> = 125°C		30	mA
I <sub>DRM</sub>	Off-state current	At V <sub>DRM</sub> , T <sub>case</sub> = 125°C		-	1	mA
dV/dt	Maximum linear rate of rise of off-state voltage	To 60% $V_{DRM}$ $T_j$ = 125°C, Gate open circuit		-	1000	V/μs
dl/dt	Rate of rise of on-state current	Gate source 20V, $20\Omega$ $t_r \le 5\mu s$ .	Non-repetitive	-	1000	A/μs
			Repetitive	-	500	A/μs
t <sub>q</sub> †	Max. gate assisted turn-off time (with feedback diode)	$\begin{split} & T_{j} = 125^{\circ}\text{C}, \ I_{\text{T(PK)}} = 200\text{A}, \\ & t_{p} = 25\mu\text{s} \ (\text{half sine wave}), \\ & V_{R} = DF451 \ \text{Diode voltage drop}, \\ & \text{dV/dt} = 600\text{V/}\mu\text{s} \ (\text{linear to }60\% \ \text{V}_{\text{DRM}}), \\ & V_{\text{GK}} = -5\text{V} \end{split}$		-	7	μѕ
t <sub>q</sub>	Max. turn-off time (with feedback diode)	$T_{j} = 125^{\circ}\text{C}$ , $I_{TM} = 100\text{A}$ , $t_{p} > 100\mu\text{s}$ , $dI_{R}/dt = 30\text{A}/\mu\text{s}$ , $V_{R} = 1\text{V}$ , $dV/dt = 600\text{V}/\mu\text{s}$ (linear to 60% $V_{DRM}$ ), Gate open.		-	10	μѕ

# **GATE TRIGGER CHARACTERISTICS AND RATINGS**

Symbol	Parameter	Conditions	Тур.	Max.	Units
V <sub>GT</sub>	Gate trigger voltage	$V_{DWM} = 12V, R_L = 3\Omega, T_{case} = 25^{\circ}C$	-	4	V
I <sub>GT</sub>	Gate trigger current	$V_{DWM} = 12V, R_L = 3\Omega, T_{case} = 25^{\circ}C$	-	250	mA
V <sub>RGM</sub>	Peak reverse gate voltage	-	-	7	V
I <sub>FGM</sub>	Peak forward gate current	-	-	10	Α
P <sub>GM</sub>	Peak gate power	-	-	50	W
P <sub>G(AV)</sub>	Average gate power	-	-	15	W

### TA329..Q

### **CURVES**

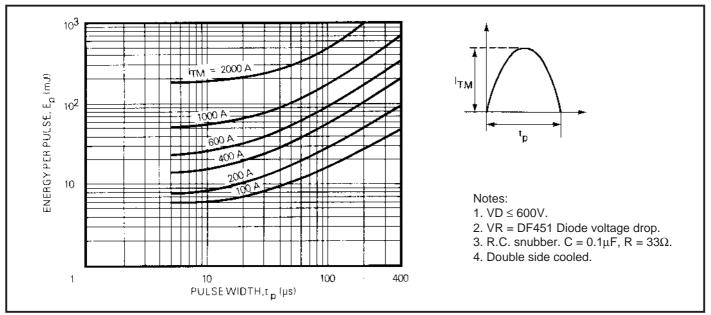


Fig.1 Energy per pulse for sinusoidal pulses.

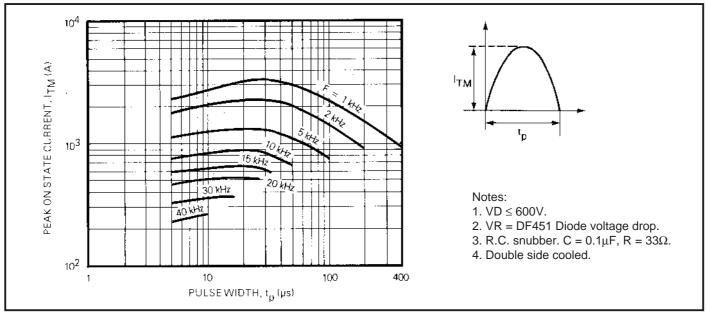


Fig.2 Maximum allowable peak on-state current vs pulse width for Tcase = 65°C.

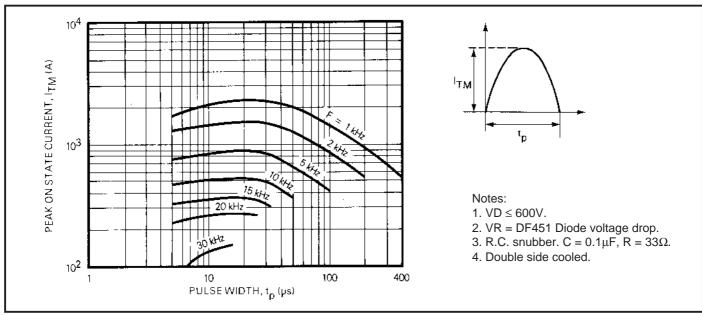


Fig.3 Maximum allowable peak on-state current vs pulse width for Tcase = 90°C.

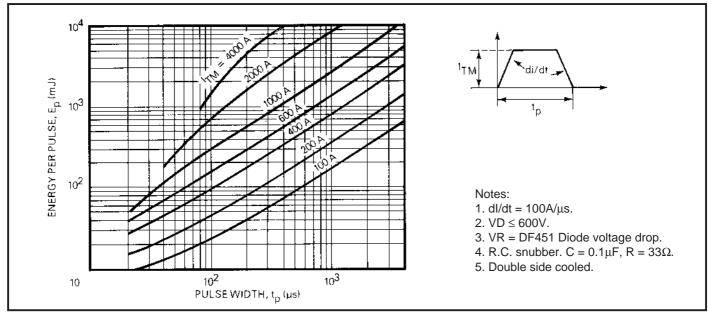


Fig.4 Energy per pulse for trapezoidal pulses

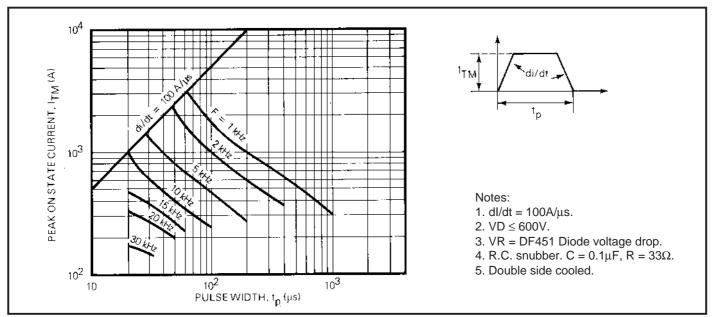


Fig.5 Maximum allowable peak on-state current vs pulse width for Tcase = 65°C.

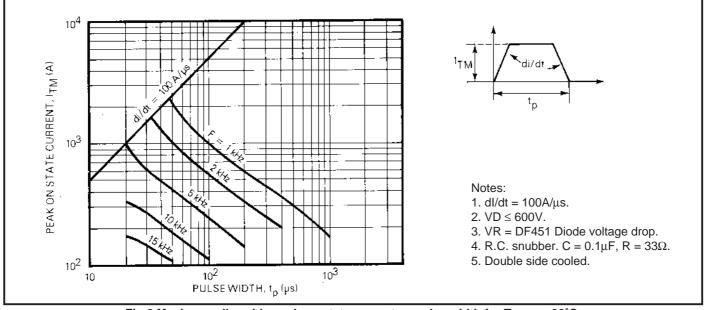


Fig.6 Maximum allowable peak on-state current vs pulse width for Tcase = 90°C.

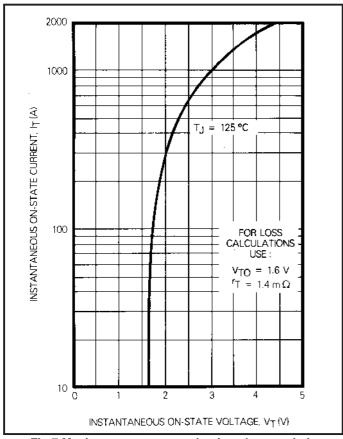


Fig.7 Maximum on-state conduction characteristic

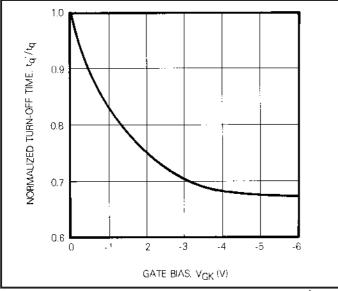


Fig.9 Typical variation of effective turn-off time  $(t_q^{\phantom{q}})$  with negative gate bias.

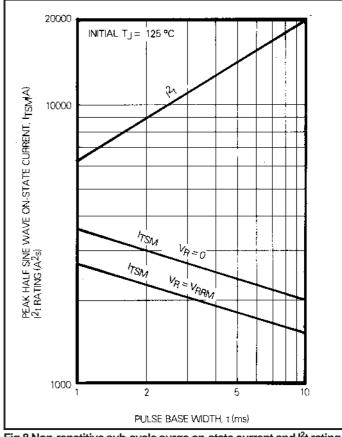


Fig.8 Non-repetitive sub-cycle surge on-state current and l<sup>2</sup>t rating.

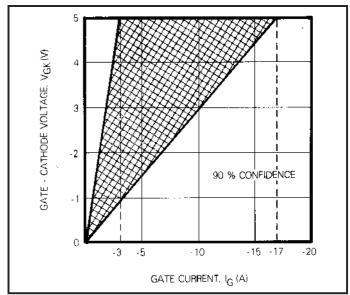


Fig.10 Reverse gate characteristics

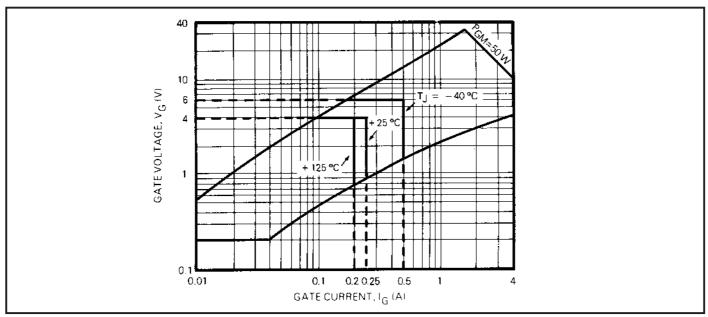


Fig.11 Gate trigger characteristics

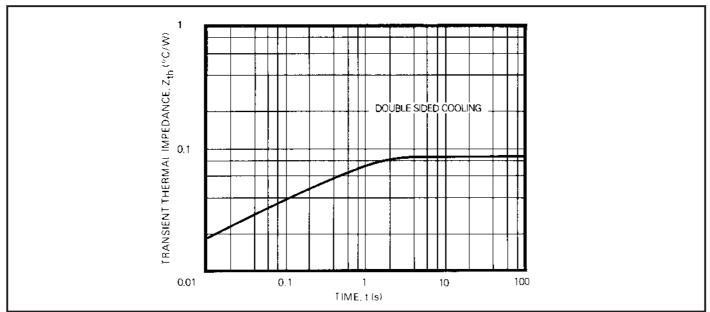
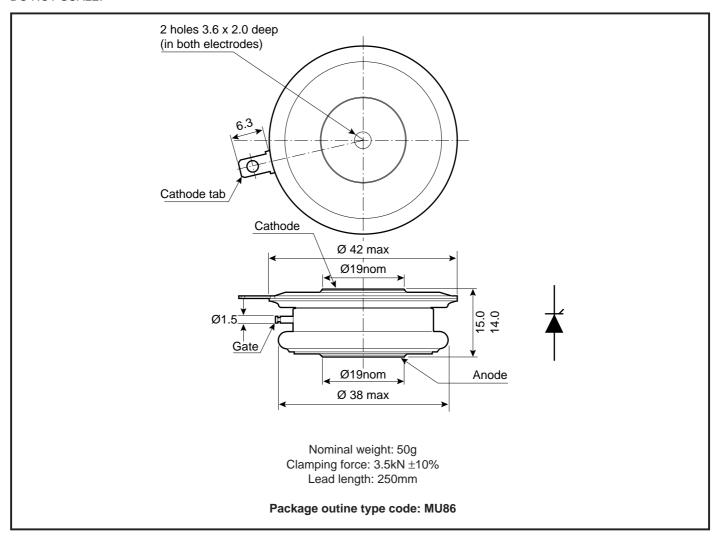


Fig.12 Transient thermal impedance - junction to case

## **PACKAGE DETAILS**

For further package information, please contact your local Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



## **ASSOCIATED PUBLICATIONS**

Title	Application Note	
	Number	
Calculating the junction temperature or power semiconductors	AN4506	
Gate triggering and the use of gate characteristics	AN4840	
Recommendations for clamping power semiconductors	AN4839	
The effect of temperature on thyristor performance	AN4870	
Thyristor and diode measurement with a multi-meter	AN4853	
Turn-on performance of thyristors in parallel	AN4999	
Use of $V_{TO}$ , $r_{T}$ on-state characteristic	AN5001	

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The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink / clamping systems in line with advances in device types and the voltage and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group continues to offer high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the up to date CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete solution (PACs).

#### **DEVICE CLAMPS**

Disc devices require the correct clamping force to ensure their safe operation. The PACs range offers a varied selection of preloaded clamps to suit all of our manufactured devices. This include cube clamps for single side cooling of 'T' 22mm

Clamps are available for single or double side cooling, with high insulation versions for high voltage assemblies.

Please refer to our application note on device clamping, AN4839

#### **HEATSINKS**

Power Assembly has it's own proprietary range of extruded aluminium heatsinks. They have been designed to optimise the performance or our semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest Sales Representative or the factory.



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Preliminary Information: The product is in design and development. The datasheet represents the product as it is understood but details may change.

Advance Information: The product design is complete and final characterisation for volume production is well in hand.

No Annotation: The product parameters are fixed and the product is available to datasheet specification.

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